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**November 2013** 

# FDP18N50 / FDPF18N50 / FDPF18N50T NChannel UniFET MOSFET 500 V, 18 A, 265

## m Features

 $\Omega RDS(on) = 220 \text{ m (Typ.)} @ VGS = 10 \text{ V, ID} = 9 \text{ A}$ 

- •Low Gate Charge (Typ. 45 nC)
- •Low Crss (Typ. 25 pF)
- •100% Avalanche Tested

## **Applications**

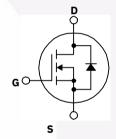
- •LCD/LED/PDP TV
- Lighting
- •Uninterruptible Power Supply

## **Description**

UniFET TMOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.







## Absolute Maximum Ratings TC = 25°C unless otherwise noted.

Symbol	Parameter	FDP18N50	FDPF18N50 / FDPF18N50T	Unit
VDSS	Drain-Source Voltage	18	V	
ID	Drain Current- Continuous (TC = 25°C) - Continuous (TC = 100°C)	10.8 72	18 * 10.8 * 72 *	A A
IDM	Drain Current- Pulsed(Note 1)	/2	,-	Α
VGSS	Gate-Source voltage	±30		V
EAS	Single Pulsed Avalanche Energy(Note 2)	945		mJ
IAR	Avalanche Current(Note 1)	18		Α
EAR	Repetitive Avalanche Energy(Note 1)	23.		mJ
dv/dt	Peak Diode Recovery dv/dt(Note 3)	5		V/ns
TJ, TSTG	Power Dissipation(TC = 25°C) - Derate Above 25°C  Operating and Storage Temperature Range	1.8	38. 5 0.3	W W/€ .C
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300		∘C

<sup>\*</sup> Drain current limited by maximum junction temperature

## **Thermal Characteristics**

Symbol	Parameter	FDP18N50	FDPF18N50 /	Unit
RθJC	Thermal Resistance, Junction-to-Case, Max.	0.53	FDPF18N50	°C/W
RθJA	Thermal Resistance, Junction-to-Ambient, Max.	62.5	3.3	°C/W

## **Package Marking and Ordering Information**

		Part Number	Top MarkPackageP	acking MethodF	Reel SizeTape Wid	IthQuantity
FDP18N50FDP18N50T	O-220TubeN/AN/A50 un	its				
FDPF18N50FDPF18N5	0TO-220FTubeN/AN/A50	units				
			FDPF18N5	OTFDPF18N50T	TO-220FTubeN/A	N/A50 units

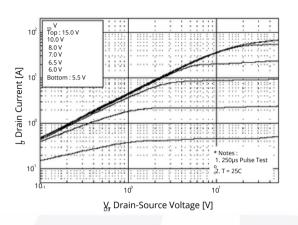
## Electrical Characteristics

	Symbol Parameter Conditions Min. Typ. Max Un
Off Characteristics	
BVDSSDrain-Source Breakdown VoltageVGS = 0 V, IΦ = 250 μA500V	
ΔBVDSSBreakdown Voltage Temperature	
/ ΔTCoefDμ°°Jficient	I = 250 A, Referenced to 25C0.5V/
IDSSZero Gate Voltage Drain CurrentVDS = 500 V, VGS = 0 V1µA	VDS = 400 V, TC = 125°C10μ
IGSSFGate-Body Leakage Current, ForwardVGS = 30 V, VDS = 0 V100nA	120 .00 1,10 .20 0 .00
IGSSRGate-Body Leakage Current, ReverseVGS = -30 V, VDS = 0 V100nA	
On Characteristics	
VGS(th)Gate Threshold VoltageVDS = VGS, ID = 250 µA3.05.0V	
RDS(on)Static Drain-Source V = 10 V   = 9 A=0.2200.265 On-Resistance GS D Ω	
gFSForward TransconductanceVDS = 40 V, ID = 9 A25S	
Dynamic Characteristics	
CissInput CapacitanceVDS = 25 V, VGS = 0 V,22002860pF	
Cf = 1 MHzossOutput Capacitance330430pF	
CrssReverse Transfer Capacitance2540pF	
Switching Characteristics	
td(on)Turn-On Delay TimeVDD = 250 V, ID = 18 A,55120ns	
tTurn-On Rise TimeVGS = 10 V, RG = 25 Ωr165340ns	
td(off)Turn-Off Delay Time95200ns	
tTurn-Off Fall Time(Note 4)f90190ns	
QgTotal Gate ChargeVDS = 400 V, ID = 18 A,4560nC	
QGate-Source ChargeVGS = 10 Vgs12.5nC	
QGate-Drain Charge(Note 4)gd19nC	
Drain-Source Diode Characteristics and Maximum Ratings	
ISMaximum Continuous Drain-Source Diode Forward Current18A	
ISMMaximum Pulsed Drain-Source Diode Forward Current72A	
VSDDrain-Source Diode Forward VoltageVGS = 0 V, IS = 18 A1.4V	
trrReverse Recovery TimeVGS = 0 V, IS = 18 A,500ps	
QReverse Recovery ChargedIF/dt =100 A/µs rr5.4µC	

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 5.2 mH, IAS = 18 A, VDD = 50 V, RG = 25  $\Omega$ , starting TJ = 25°C.
- 3. ISD  $\leq$  18 A, di/dt  $\leq$  200 A/µs, VDD  $\leq$  BVDSS, starting TJ = 25°C. 4. Essentially independent of operating temperature typical characteristics.

## **Typical Performance Characteristics**

**Figure 1. On-Region Characteristics** 



**Figure 2. Transfer Characteristics** 

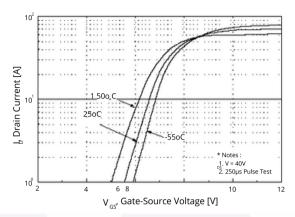
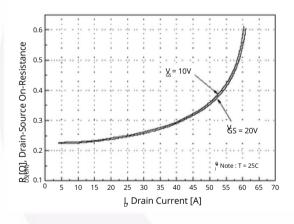
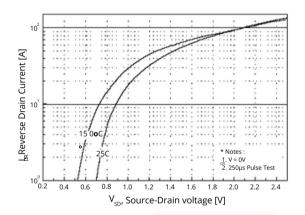


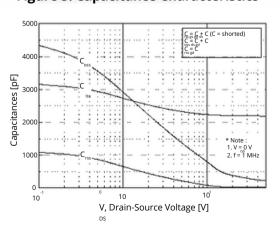
Figure 3. On-Resistance Variation vs. Figure 4. Body Diode Forward Voltage Drain Current and Gate Voltage Variation vs. Source Current

## and Temperatue

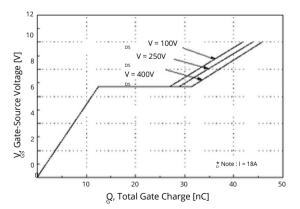




**Figure 5. Capacitance Characteristics** 

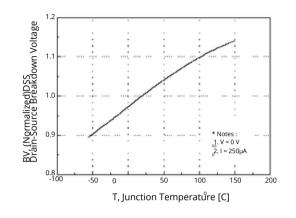


**Figure 6. Gate Charge Characteristics** 



## Typical Performance Characteristicscontinued)

# Figure 7. Breakdown Voltage VariationFigure 8. On-Resistance Variation vs. Temperature vs. Temperature



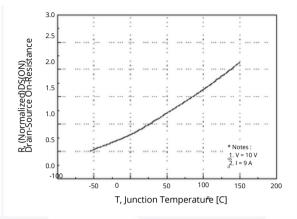
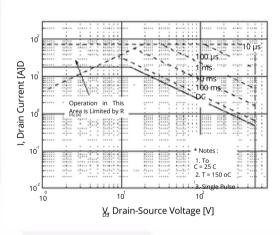


Figure 9-1. Maximum Safe Operating Area Figure 9-2. Maximum Safe Operating Area - FDP18N50 - FDPF18N50 / FDPF18N50T



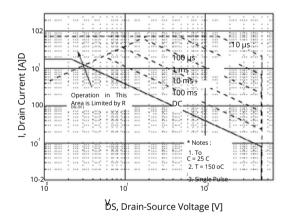
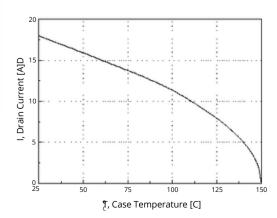


Figure 10. Maximum Drain Current vs. Case Temperature



## Typical Performance Characteristics ontinued)

Figure 11-1. Transient Thermal Response Curve - FDP18N50

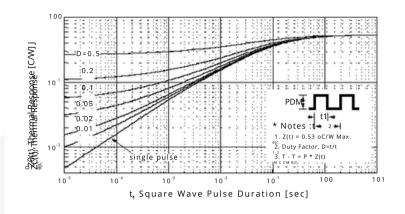
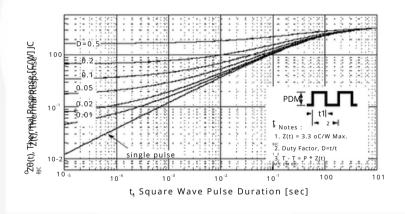


Figure 11-2. Transient Thermal Response Curve - FDPF18N50 / FDPF18N50T



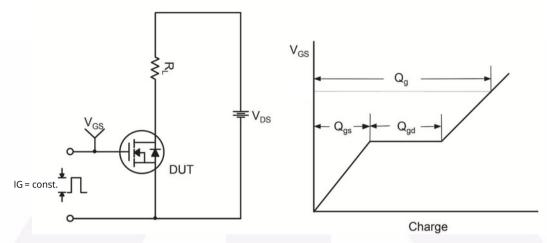


Figure 12. Gate Charge Test Circuit & Waveform

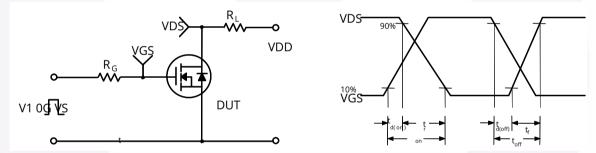


Figure 13. Resistive Switching Test Circuit & Waveforms

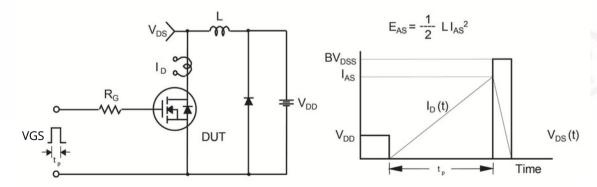


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

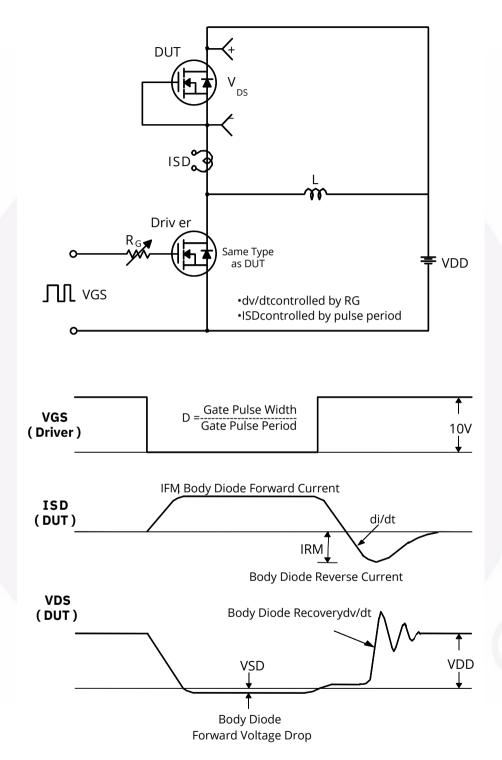


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

## **Mechanical Dimensions**

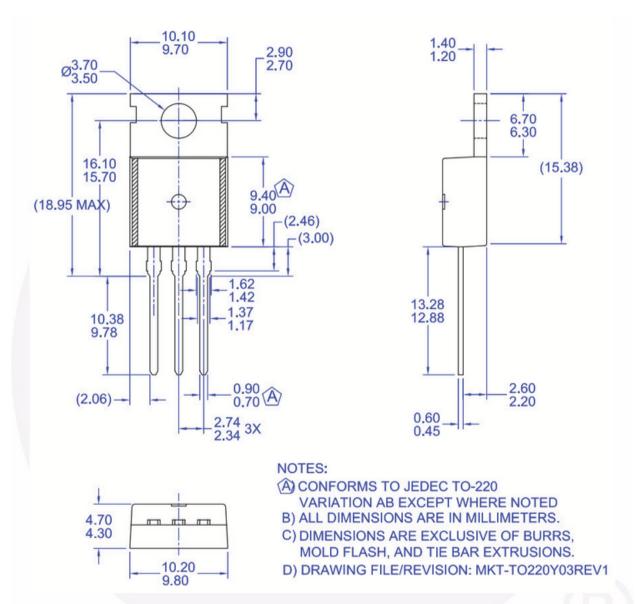


Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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## **Mechanical Dimensions**

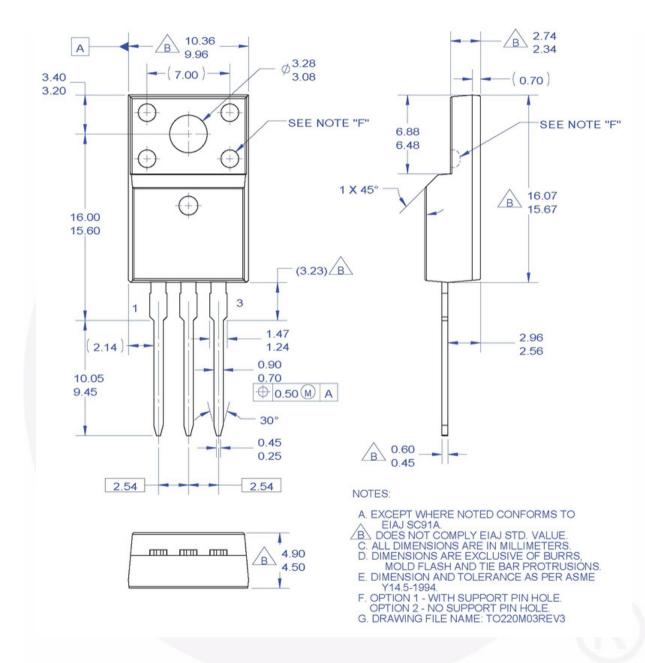


Figure 17. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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